

L Number	Hits	Search Text	DB	Time stamp
1	1	(fang-jui-hua chung-cheng-hui lu-chia-hui).in. and barrier	USPAT; US-PGPUB; EPO; DERWENT	2004/03/03 09:29
2	10	(second adj1 barrier) same ((anneal\$3 treat\$3 heat\$3) with (nitrogen (nitrous adj1 oxide))).bi.	USPAT; US-PGPUB	2004/03/03 12:51
3	604	(second adj1 barrier) with ("Cu/Al/Si" "Cu/Al" wiring conduct\$3).bi.	USPAT; US-PGPUB	2004/03/03 10:30
4	418	(second adj1 barrier) with ("Cu/Al/Si" "Cu/Al" wiring conduct\$3).bi.	USPAT	2004/03/03 10:30
5	107	((metal conductive) adj1 (wiring layer film)) with barrier) same ((anneal\$3 treat\$3) with nitrogen).bi.	USPAT; US-PGPUB	2004/03/03 12:01
6	6	007304.ap.	USPAT; US-PGPUB	2004/03/03 12:01
7	35180	(anneal\$3 treat\$3 heat\$3) with (bak\$3 (ion adj1 bump\$3) quench\$3).bi.	USPAT; US-PGPUB	2004/03/03 12:52
8	340	((anneal\$3 treat\$3 heat\$3) with (bak\$3 (ion adj1 bump\$3) quench\$3)) same barrier.bi.	USPAT; US-PGPUB	2004/03/03 13:30
9	0	((anneal\$3 treat\$3 heat\$3) with (bak\$3 (ion adj1 bump\$3)) with quench\$3) same barrier.bi.	USPAT; US-PGPUB	2004/03/03 13:15
10	0	((anneal\$3 treat\$3 heat\$3) with (bak\$3 (ion adj1 bump\$3)) with quench\$3) and barrier.bi.	USPAT; US-PGPUB	2004/03/03 13:15
13	0	(quench\$3 and bak43 and barrier).bi.	USPAT; US-PGPUB	2004/03/03 13:17
14	1262	(quench\$3 and bak\$3 and barrier).bi.	USPAT; US-PGPUB	2004/03/03 13:18
15	58	(quench\$3 same bak\$3) and barrier.bi.	USPAT; US-PGPUB	2004/03/03 13:18
16	10	((anneal\$3 treat\$3 heat\$3) with nitrogen with quench\$3) same barrier.bi.	USPAT; US-PGPUB	2004/03/03 13:27
17	158	((anneal\$3 treat\$3 heat\$3) with quench\$3) same barrier.bi.	USPAT; US-PGPUB	2004/03/03 13:30
18	162	((anneal\$3 treat\$5 heat\$3) with quench\$3) same barrier.bi.	USPAT; US-PGPUB	2004/03/03 13:31